# Silicon Sentry

**HOLOEYE's Sensors Division** 



# **Core Technology**

All sensor applications have one common requirement: a reliable sensing component. The ability to micromachine sensor chips using standard silicon wafer technologies enables Holoeye Systems / to produce consistently reliable sensors in high volumes for mass market applications.

Holoeye Systems offers an array of products and technologies centered around integrated MEMS components, UV-IR optical components, and seamless ortho-planer designs.

Appropriately titled, Silicon Sentry, Holoeye Systems' line of MEM's based autonomous RFID enabled Chemical, Physical, and/or Biological sensors are ideal for monitoring critical processes and/or/assets within/Home Land Security, Defense, and Corporate/Personal Equipment Preservation market segments. Silicon Sentry is adequately equipped to be either your first or last line of defense.



# A brief list of our technologies includes:

- Chemical Sensors
- Radiation Sensors
- Temperature Sensors
- Pressure Sensors
- Flow Sensors
- Density Sensors
- Micro Sampling Systems (Microsensors, Micropumps, Microvalves, Micropyrolyzers)

Each Chemical Silicon Sentry relies on a high-performance micro machined IRMOS (Infra-Red/ Metal Oxide Semiconductor) sensor. The sensor system is produced by combining the advancements of thin film technology with patent pending IR technologies on a silicon substrate, hence the name, Silicon Sentry.

Using concentration-dependent chemisorption conductivity, and both molecular sieve and affinity thin-film technologies, each sensor has high sensitivity and selectivity to a specific target.

#### Services

The basis for our service and technologies are focused around Integrated MEMS components, UV-IR optical components and highly integrated & seamless Ortho-Planer designs.

- OEM & Custom Design
- OEM Sub-Modules

# **Key Benefits**

- · High Sensitivity to Oxidizing & Reducing Gas Binaries CO (0.5 to 500 ppm) / CH<sub>4</sub>(100 to 100,000 ppm) / NO<sub>2</sub> (0.1 to 2 ppm) / SO<sub>2</sub> (.01 to 500 ppm)
- Low Power Consumption
- Long Lifetime
- · Low Cross Sensitivity
- · Long-term Stability

# **Common Analytes**

Carbon Monoxide

Nitrogen Oxide

Sulfur Dioxide

Methane

Hydrocarbons (Ch2-10)

Alcohols

Ammonia

Butane

**Bromine** 

Chlorine

Ethylene

Fluorine

Hydrogen

Hydrogen Sulfide

COS

LPG

Phosgene

Nitrogen Dioxide

Ozone

Toluene

**VOCs** 

Oxygen

Carbon Dioxide



### **Features**

**Dimensions:** Chip size: 2x2mm x 250um

Operation Temperature Range: (CO - 250°C - 300°C), (NO<sub>2</sub> - 250°C - 350°C), (CH<sub>4</sub> - 300°C - 350°C), (SO<sub>2</sub> - 300°C - 400°C)

Typical Operation Temperature: (CO - 270°C), (NO2 - 270°C), (CH<sub>4</sub> - 320°C), (SO<sub>2</sub> - 385°C)

**Ambient Temperature Range:** -40°C - 125°C (lower than op. temp.)

Ambient Humidity: 0 - 95% RH

**Power Consumption:** <35 mW @ 2.3 - 3.0Vdc (15-20ma)

Signal Output Component: Resistance

Typical Heater Voltage: (CO /2.3 V for 270°C), (NO<sub>2</sub> /2.3 V for 270°C), (CH<sub>4</sub> /2.7 V for 320°C), (SO<sub>2</sub> /2.85 V for 350°C)

Temperature Coefficient rel. to R(20°C): TC≈1700 ppm/K

Typical Heater Resistance at RT:  $95 \Omega$ 

Concentration Range: Can withstand (1% CO), (>10ppm NO<sub>2</sub>), (10% CH<sub>4</sub>), (1% SO<sub>2</sub>) in air

Sensitivity Range: (CO /0.5 - 500 ppm), (NO2 /0.1 - 2 ppm), (CH<sub>4</sub> /0.01 - 10 %), (SO<sub>2</sub> /10ppb - 1500 ppm)

**Typical Response / Recovery Time:** milliseconds **Expected Lifetime:** 5-10 Years dependant upon application

Cross Sensitivity: Limited cross sensitivity, target gas selectivities are tuned by affinity catalyst applied to sensing membrane

Packaging Options: ASIC Modules, Chip-on-Board, MEMS die, MTO-39 & SOIC package with protection membrane.

#### **Silicon Sentry**

- · Well suited for detection of carbon monoxide, volatile organic compounds, volatile sulfur compounds or nitrogen dioxide.
- · Fast response: ~ 1 sec
- · Hardware: circuitry for 2 micro-machined sensor elements with micro-controller.
- · Firmware: raw data output or quantification of measured variable, measurement interval ~200 ms
- · Housing: polyamide with diffusion membrane (ultrasonic welding) and cover (laser welding)
- Output: PWM or RS232 via MQS connector, PWM may be converted to voltage or 4-20ma output. "WiFi optional". The newest protocol is the "POE", power-over-ethernet a plug & play solution.

# Hardware Description:

# - HT-PCB with SMD electronics

- Circuitry for 2 IRMOS sensor elements
- Micro-controller for data processing
- PWM or RS232 output

## **Customization:**

- Number of sensor elements needed
- Sensing material selection

# Firmware Description:

- Functionality to drive sensors
- Alternate control for pumps, valves, etc..
- Algorithm for baseline correction and quantification
- Algorithm for self-diagnosis, Built-In-Self-Test

## **Customization:**

Application-specific:

- Operation parameters for sensor elements
- Interval time, sampling to match process
- Algorithm output, corrected engineering units
- Output format and protocol, support most telemetries
- Addition of selective hydrophobic membrane technology
- Accessories to enable operation in liquids, solids, or any aggressive matrix.

#### **Applications:**

- VOC for residual solvent hazardous leak detection
- Flue-stack, water quality, Bio-waste storage
- On-line & off-line quantitative & qualitative process analysis
- Refinery, pipeline, transport & refueling stations
- Paper-pulp, polymer process, winery & semiconductor process
- Smart armor
- Air quality control systems
- Asset preservation

